Trit: mm

1: Anode 2: Cathode 3: Emitter 4: Collector

PRSMW104-002 Package

plerance unless otherwise specified is ±0.2

CNB1011

Reflective photosensor

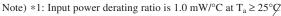
Non-contact point SW, object sensing

■ Features

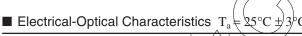
• Ultraminiature, thin type: 2.29 mm × 2.9 mm (height: 0.88 mm)

■ Absolute Maximum Ratings $T_a = 25$ °C

	Symbol	Rating	Unit	
Input (Light	Reverse voltage	V _R	6	V
emitting diode)	Forward current	I_{F}	30	mA
	Power dissipation *1	P_{D}	75	mW
Output (Photo transistor)	Collector-emitter voltage (Base open)	V _{CEO}	35	V
	Emitter-collector voltage (Base open)	V _{ECO}	6	v
	Collector current	I_{C}	20	mA
	Collector power dissipation *2	P _C	75	mW(
Temperature	Operating ambient temperature	T _{opr}	-25 to +85	°¢/
	Storage temperature	T _{stg}	-40 to +100	//c



^{*2:} Output power derating ratio is 1.0 mW/°C at $T_a \ge 25$ /°C.

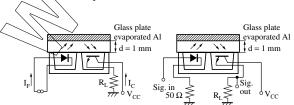


	Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input	Forward voltage	V_F	$I_{\kappa} = 4 \text{ mA}$		1.15	1.30	V
characteristics	Reverse current	I_R	$V_R = 3 \text{ V}$			10	μА
Output	Collector-emitter cutoff current	I _{CEO}	$V_{QE} \neq 20 \text{ V}$			100	nA
characteristics	(Base open)						
Transfer	Collector current *1	I_{C}	$V_{CE} = 2 \text{ V}, I_F = 4 \text{ mA}, d = 1 \text{ mm}$	40		243	μΑ
characteristics	Dark current	$\bigcirc I_D$	$V_{CE} = 2 \text{ V}, I_F = 4 \text{ mA}$			100	nA
	Collector-emitter saturation voltage	V _{CE(sat)}	$I_F = 20 \text{ mA}, I_C = 0.1 \text{ mA}$			0.4	V
	Rise time *Z	t _r	$V_{CC} = 2 \text{ V}, I_C = 0.1 \text{ mA}$		40		μs
	Fall time *2	$t_{\rm f}$	$R_L = 1000 \ \Omega$		50		μs

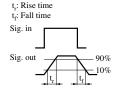
Note) 1. Input and output are handled electrically.

2. This product is not designed to withstand radiation

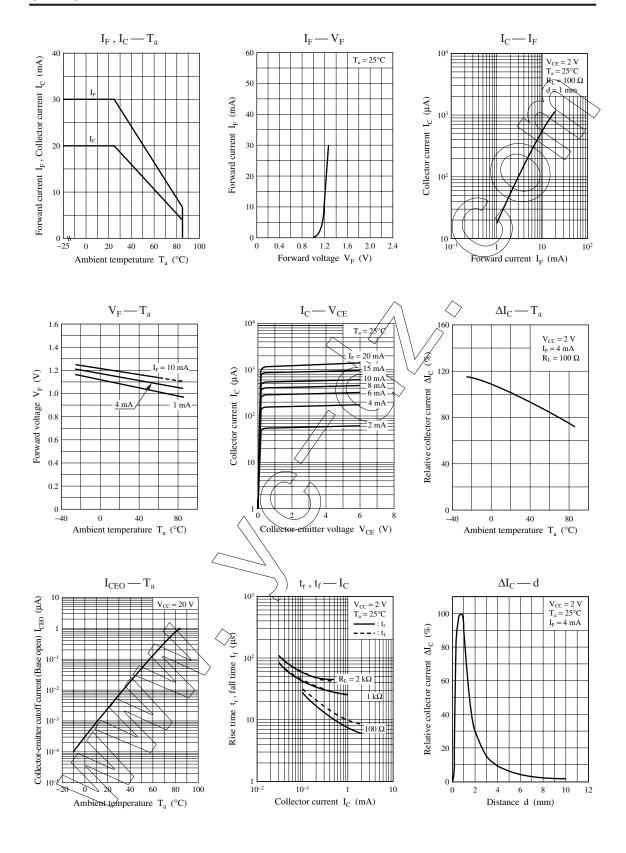
3. *1: Output current measurement method



*2: Switching time measurement circuit



Publication date: April 2004 SHG00056BED 1



Caution for Safety

⚠ DANGER

■ This product contains Gallium Arsenide (GaAs).

GaAs powder and vapor are hazardous to human health if inhaled or ingested. Do not burn, destroy, cut, cleave off, or chemically dissolve the product. Follow related laws and ordinances for disposal. The product should be excluded form general industrial waste or household garbage.

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- Any applications other than the standard applications intended.

physical injury, fire, social damages, for example, by using the products.

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